

✓ 13. The method of claim 9 wherein:

the patterned mask layer has a linewidth of from about 0.04 to about 0.13 microns;

the etch residue layer has a linewidth of from about 0.01 to about ^{0.03}~~0.02~~ microns; and

the laterally increased etch residue layer has a linewidth of from about 0.02 to about ^{0.06}~~0.04~~ microns.

14. The method of claim 9 wherein the etch residue layer is formed intrinsic to the plasma etch method.

15. A method for forming a gate electrode comprising:

providing a semiconductor substrate;

forming over the semiconductor substrate a blanket gate electrode material layer;

forming upon the blanket gate electrode material layer a patterned mask layer;

16. The method of claim 15 wherein the etch residue layer and the laterally increased etch residue layer are formed of a fluoropolymer etch residue material.

17. The method of claim 15 wherein the patterned mask layer is removed employing the plasma etch method.

18. The method of claim 15 wherein the patterned mask layer is removed independent of the plasma etch method.

β 19. The method of claim 15 wherein:
the patterned mask layer has a linewidth of from about 0.04 to about 0.13 microns;
the etch residue layer has a linewidth of from about 0.01 to about 0.03 microns; and
the laterally increased etch residue layer has a linewidth of from about 0.02 to about 0.06 microns.

20. The method of claim 15 wherein the etch residue layer is formed intrinsic to the plasma etch method.